



**AO4826**

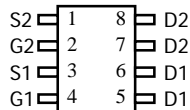
**Dual N-Channel Enhancement Mode Field Effect Transistor**

**General Description**

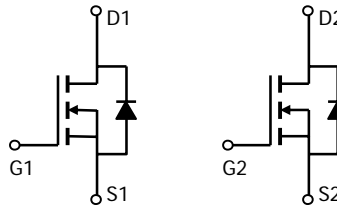
The AO4826 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO4826 is Pb-free (meets ROHS & Sony 259 specifications).*

**Features**

- $V_{DS}$  (V) = 60V
- $I_D$  = 6.3A ( $V_{GS}$  = 10V)
- $R_{DS(ON)} < 25m\Omega$  ( $V_{GS}$  = 10V)
- $R_{DS(ON)} < 30m\Omega$  ( $V_{GS}$  = 4.5V)



**SOIC-8**



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ\text{C}$	6.3	A
	$T_A=70^\circ\text{C}$	5	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	40	
Power Dissipation	$T_A=25^\circ\text{C}$	2	W
	$T_A=70^\circ\text{C}$	1.28	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	50	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	73	
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	31	40	$^\circ\text{C/W}$

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	2.1	3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	40			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6.3A T <sub>J</sub> =125°C		20 34	25 42	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.7A		22	30	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =6.3A		27		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.74	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				3	A
I <sub>SM</sub>	Pulsed Body Diode Current <sup>B</sup>				40	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, f=1MHz		1920	2300	pF
C <sub>oss</sub>	Output Capacitance			155		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			116		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		0.65	0.8	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =6.3A		47.6	58	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			24.2	30	nC
Q <sub>gs</sub>	Gate Source Charge			6		nC
Q <sub>gd</sub>	Gate Drain Charge			14.4		nC
t <sub>D(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, R <sub>L</sub> =4.7Ω, R <sub>GEN</sub> =3Ω		7.6		ns
t <sub>r</sub>	Turn-On Rise Time			5		ns
t <sub>D(off)</sub>	Turn-Off Delay Time			28.9		ns
t <sub>f</sub>	Turn-Off Fall Time			5.5		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =6.3A, dI/dt=100A/μs		33.2	40	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =6.3A, dI/dt=100A/μs		43		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

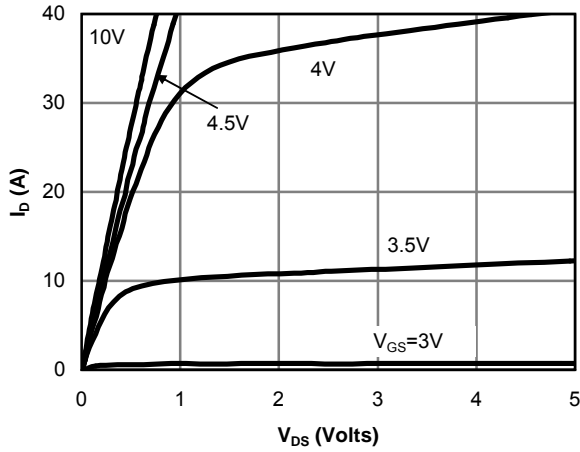


Fig 1: On-Region Characteristics

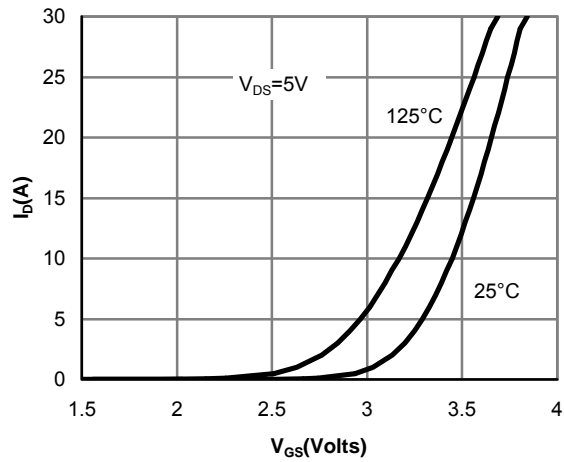


Figure 2: Transfer Characteristics

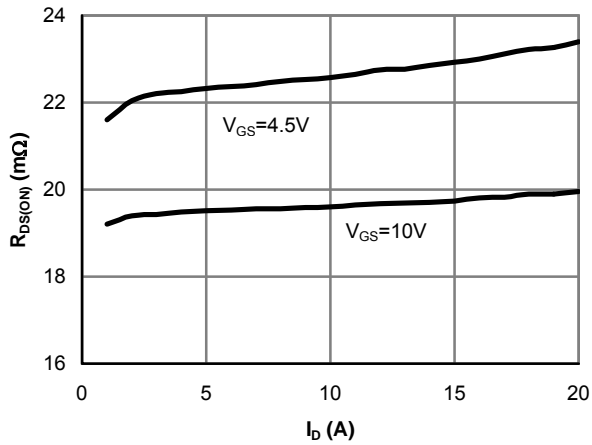


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

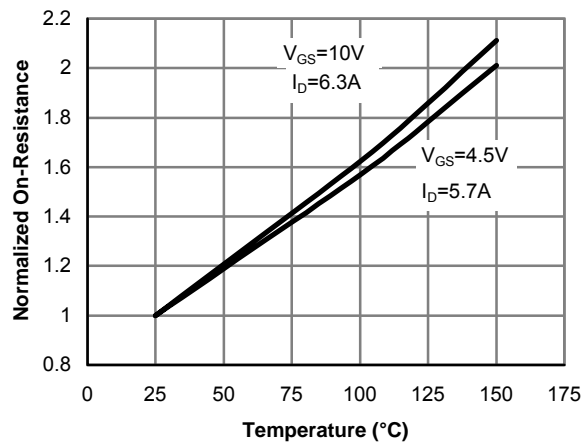


Figure 4: On-Resistance vs. Junction Temperature

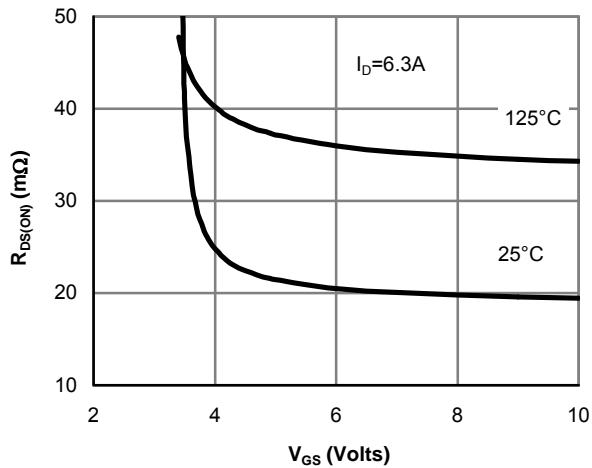


Figure 5: On-Resistance vs. Gate-Source Voltage

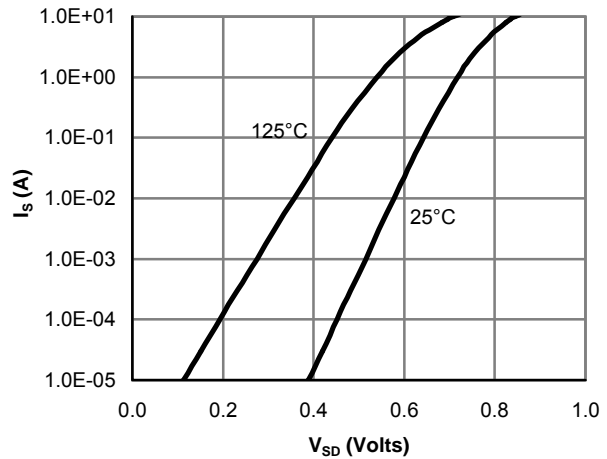


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

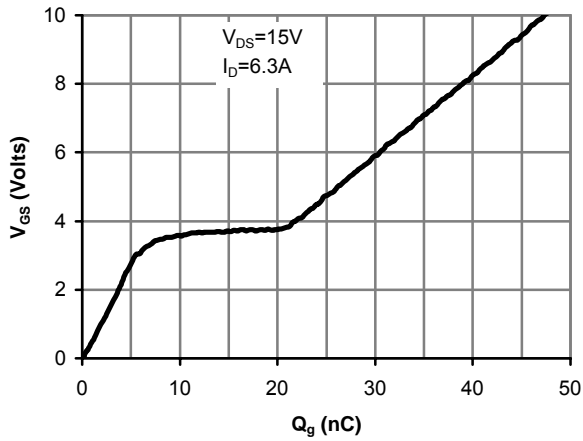


Figure 7: Gate-Charge Characteristics

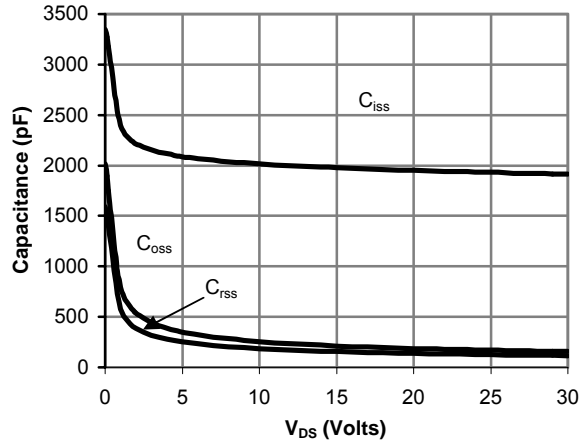


Figure 8: Capacitance Characteristics

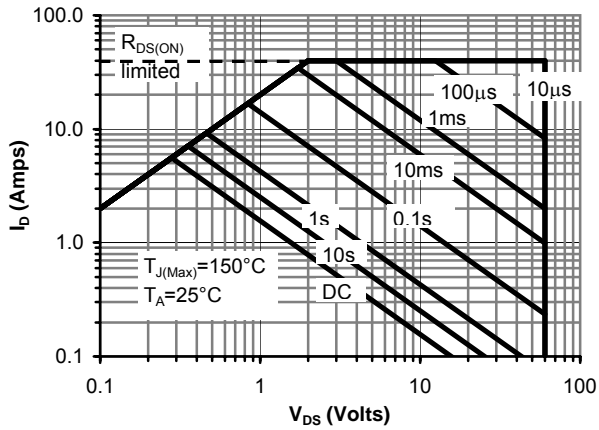


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

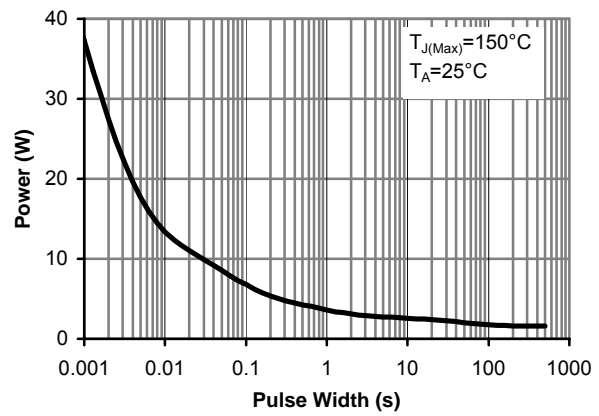


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

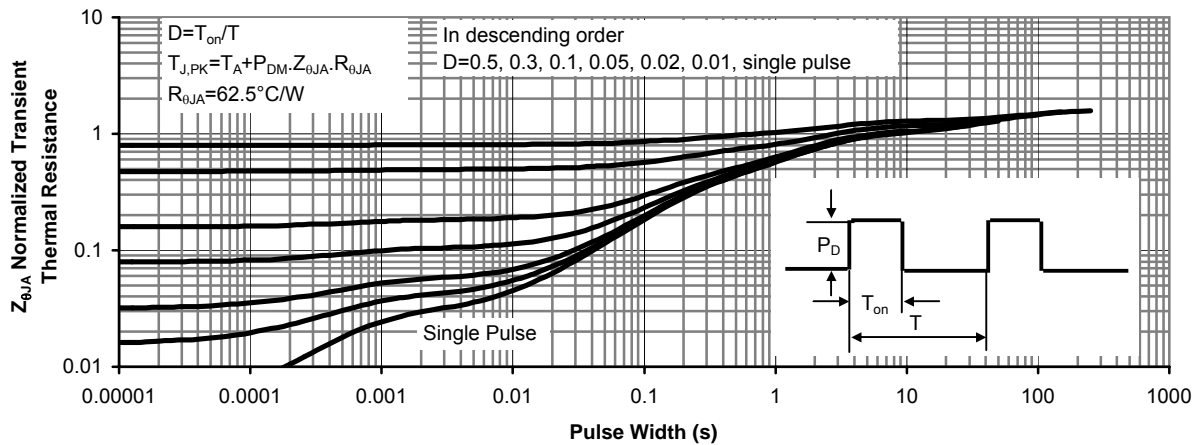


Figure 11: Normalized Maximum Transient Thermal Impedance